

# HSB226WK

Silicon Schottky Barrier Diode

# HITACHI

ADE-208-827 (Z)  
Rev 0  
Nov. 1999

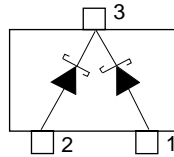
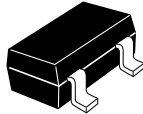
## Features

- Low reverse current, Low capacitance.
- CMPAK Package is suitable for high density surface mounting and high speed assembly.

## Ordering Information

Type No.	Laser Mark	Package Code
HSB226WK	E6	CMPAK

## Outline



(Top View)

- 1 Anode
- 2 Anode
- 3 Cathode

## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	25	V
Non-Repetitive peak forward surge current	$I_{FSM}^{*1,2}$	200	mA
forward current	$I_F^{*2}$	50	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Notes: 1. 10msec sine wave 1 pulse

Notes: 2. Two device total

## Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_{F1}$	—	—	0.33	V	$I_F = 1 \text{ mA}$
	$V_{F2}$	—	—	0.38	V	$I_F = 5 \text{ mA}$
Reverse current	$I_R$	—	—	0.45	$\mu\text{A}$	$V_R = 20\text{V}$
Capacitance	C	—	—	2.80	pF	$V_R = 1\text{V}, f = 1 \text{ MHz}$

Note: 1. Per one device

Main Characteristic

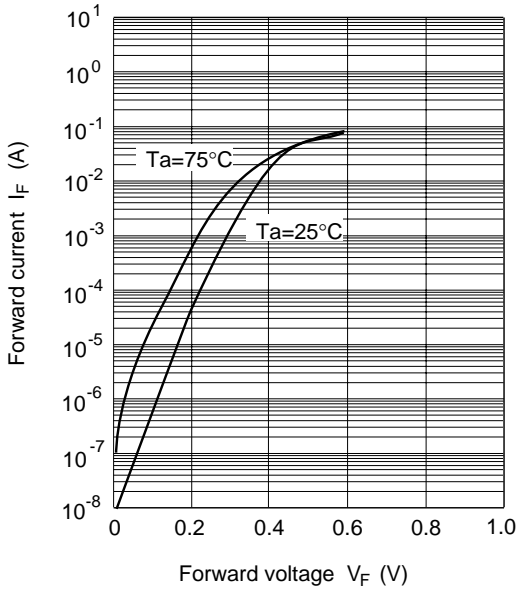


Fig.1 Forward current Vs. Forward voltage

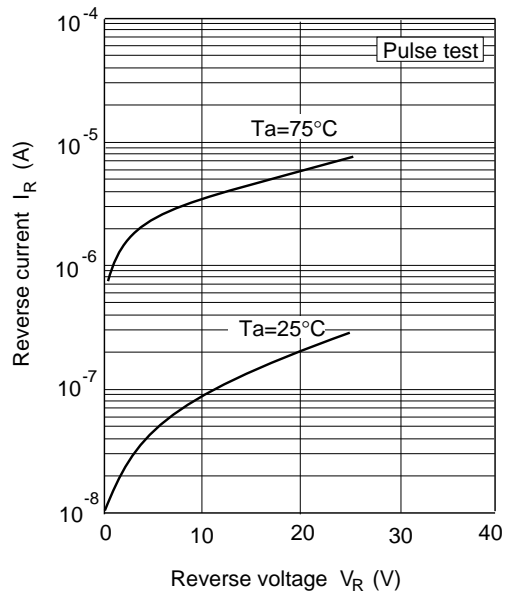


Fig.2 Reverse current Vs. Reverse voltage

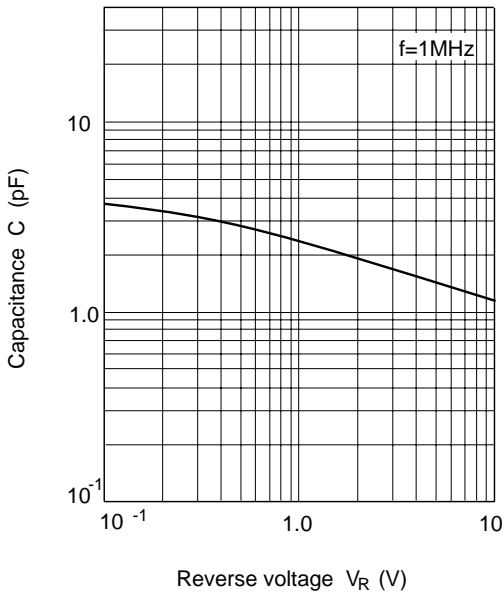
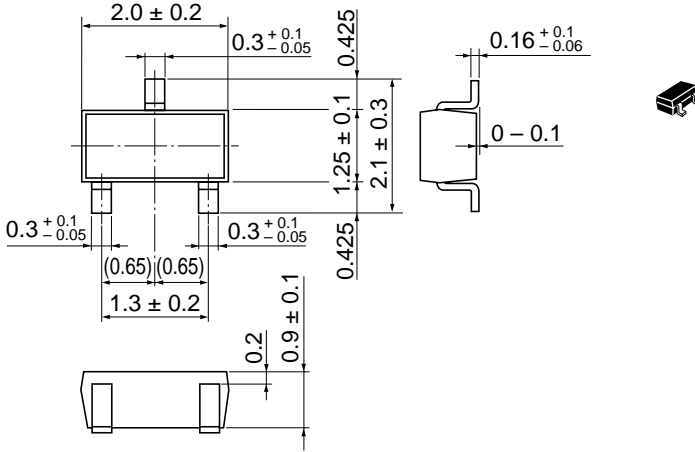


Fig.2 Capacitance Vs. Reverse voltage

## Package Dimensions

Unit: mm



Hitachi Code	CMPAK
JEDEC	—
EIAJ	Conforms
Mass	0.006 g

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